

### N-channel TrenchMOS intermediate level FET

Rev. 1 — 18 August 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

### 1.4 Quick reference data

#### Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

| Parameter                              | Conditions   |  | Min  | Тур  | Max   | Unit  |
|--|--|--|--|--|---|---|
| drain-source<br>voltage                | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  |  | -  | -  | 40  | V   |
| drain current                          | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C;<br>see <u>Figure 1</u>  | [1]  | -  | -  | 120   | A   |
| total power<br>dissipation             | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   |  | -  | -  | 306   | W   |
| racteristics                           |  |  |  |  |   |   |
| drain-source<br>on-state<br>resistance | $V_{GS}$ = 10 V; $I_D$ = 25 A;<br>$T_j$ = 25 °C; see <u>Figure 11</u>  |  | -  | 1.6  | 1.9   | mΩ  |
|  | Parameter   drain-source   voltage   drain current   total power   dissipation   tracteristics   drain-source   on-state | $\begin{array}{ll} \mbox{drain-source} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} \\ \mbox{oltage} & \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \\ \mbox{see} \ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $ | $\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C \\ \hline voltage & & & \\ \hline drain \ current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; & & \\ \hline see \ Figure \ 1 & & \\ \hline total \ power & & \\ \hline drain \ source & & \\ \hline mathbf{aracteristics} & & \\ \hline drain-source & & V_{GS} = 10 \ V; \ I_D = 25 \ A; \\ \hline on-state & & T_j = 25 \ ^\circ C; \ see \ Figure \ 11 & \\ \hline \end{array}$ | $\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C & - \\ \hline voltage & & & \\ \hline drain \ current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; & & \\ \hline see \ \hline Figure \ 1 & & \\ \hline total \ power & & \\ \hline drain \ source & T_{mb} = 25 \ ^\circ C; \ see \ \hline Figure \ 2 & - \\ \hline ext{and} \ racteristics & & \\ \hline drain-source & V_{GS} = 10 \ V; \ I_D = 25 \ A; & - \\ \hline on-state & & T_j = 25 \ ^\circ C; \ see \ \hline Figure \ 11 & & \\ \hline ext{and} \ Figure \ 11 & & \\ \hline ext{and} $ | ParameterConditionsMinTypdrain-source<br>voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $V_{GS} = 10 \ V; T_{mb} = 25 \ ^{\circ}C;$ [1]drain current $V_{GS} = 10 \ V; T_{mb} = 25 \ ^{\circ}C;$ see Figure 1total power<br>dissipation $T_{mb} = 25 \ ^{\circ}C;$ see Figure 2tracteristicsdrain-source<br>on-state $V_{GS} = 10 \ V; \ I_D = 25 \ A;$<br>$T_j = 25 \ ^{\circ}C;$ see Figure 11-1.6 | ParameterConditionsMinTypMaxdrain-source<br>voltage $T_j \ge 25 \ ^\circ\text{C}; \ T_j \le 175 \ ^\circ\text{C}$ 40drain current $V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ\text{C};$ [1]120drain current $V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ\text{C};$ [1]306total power<br>dissipation $T_{mb} = 25 \ ^\circ\text{C};$ see Figure 2306tracteristicsdrain-source<br>on-state $V_{GS} = 10 \ V; \ I_D = 25 \ A;$<br>$T_j = 25 \ ^\circ\text{C};$ see Figure 11-1.61.9 |



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| Symbol               | Parameter  | Conditions   | Min | Тур | Max  | Unit |
|----------------------|--|--|-----|-----|------|------|
| Avalanche            | e ruggedness                                       |  |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $ \begin{split} I_D &= 120 \text{ A};  \text{V}_{sup} \leq 40 \text{ V}; \\ R_{GS} &= 50  \Omega;  \text{V}_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $ | -   | -   | 1.02 | J    |
| Dynamic of           | characteristics                                    |  |     |     |      |      |
| Q <sub>GD</sub>      | gate-drain charge                                  | $\begin{split} I_D &= 25 \text{ A}; V_{DS} = 32 \text{ V}; \\ V_{GS} &= 10 \text{ V}; \text{ see } \underline{Figure \ 13}; \\ \text{see } \underline{Figure \ 14} \end{split}$                              | -   | 72  | -    | nC   |

[1] Continuous current is limited by package.

### 2. Pinning information

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | G       | gate                              |                    | -              |
| 2        | D       | Drain                             | mb                 |                |
| 3        | S       | source                            |                    |                |
| mb       | D       | mounting base; connected to drain |                    | mbb076 S       |
|          |         |                                   | SOT404 (D2PAK)     |                |

### 3. Ordering information

| Table 3. Ordering | information |  |         |
|-------------------|-------------|--|---------|
| Type number       | Package     |  |         |
|                   | Name        | Description  | Version |
| BUK661R9-40C      | D2PAK       | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                       | Conditions  |                  | Min | Max  | Unit |
|----------------------|---|---|------------------|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                            | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   |                  | -   | 40   | V    |
| V <sub>GS</sub>      | gate-source voltage                             | Pulsed  | <u>[1]</u>       | -20 | 20   | V    |
|                      |   | DC  | [2]              | -16 | 16   | V    |
| I <sub>D</sub>       | drain current                                   | $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$  | [3]              | -   | 120  | А    |
|                      |   | $T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see Figure 1  | [3]              | -   | 120  | А    |
| I <sub>DM</sub>      | peak drain current                              | $T_{mb} = 25 \text{ °C}; t_p \le 10  \mu\text{s}; \text{ pulsed};$ see Figure 3   |                  | -   | 1107 | A    |
| P <sub>tot</sub>     | total power dissipation                         | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |                  | -   | 306  | W    |
| T <sub>stg</sub>     | storage temperature                             |   |                  | -55 | 175  | °C   |
| Tj                   | junction temperature                            |   |                  | -55 | 175  | °C   |
| Source-drai          | in diode  |   |                  |     |      |      |
| ls                   | source current                                  | T <sub>mb</sub> = 25 °C   | [3]              | -   | 120  | А    |
| I <sub>SM</sub>      | peak source current                             | $t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$  |                  | -   | 1107 | А    |
| Avalanche r          | ruggedness                                      |   |                  |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source<br>avalanche energy | $\label{eq:ld} \begin{array}{l} I_{D} = 120 \; A; \; V_{sup} \leq 40 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$ |                  | -   | 1.02 | J    |
| E <sub>DS(AL)R</sub> | repetitive drain-source<br>avalanche energy     |   | <u>[4][5][6]</u> | -   | -    | J    |

[1] Accumulated pulse duration not to exceed 5mins.

[2] -16V accumulated duration not to exceed 168 hrs

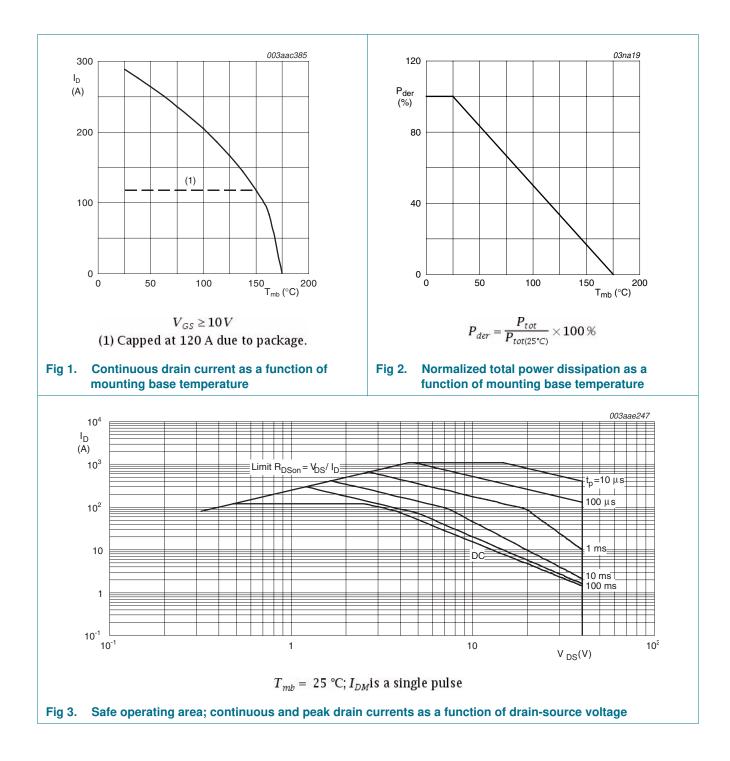
[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

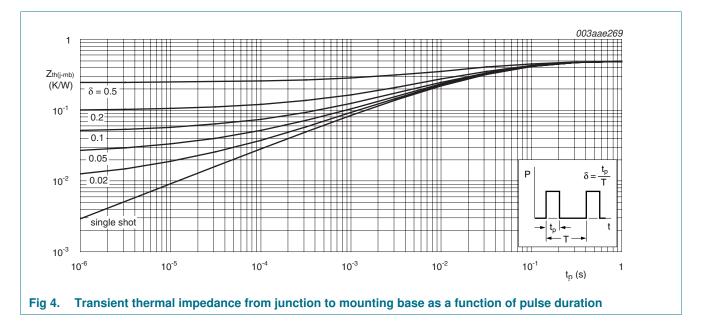
## BUK661R9-40C



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#### **Thermal characteristics** 5.

| Table 5.             | Thermal characteristics                           |                      |     |     |      |      |
|----------------------|---|----------------------|-----|-----|------|------|
| Symbol               | Parameter   | Conditions           | Min | Тур | Max  | Unit |
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4         | -   | -   | 0.49 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       | vertical in free air | -   | 60  | -    | K/W  |



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### 6. Characteristics

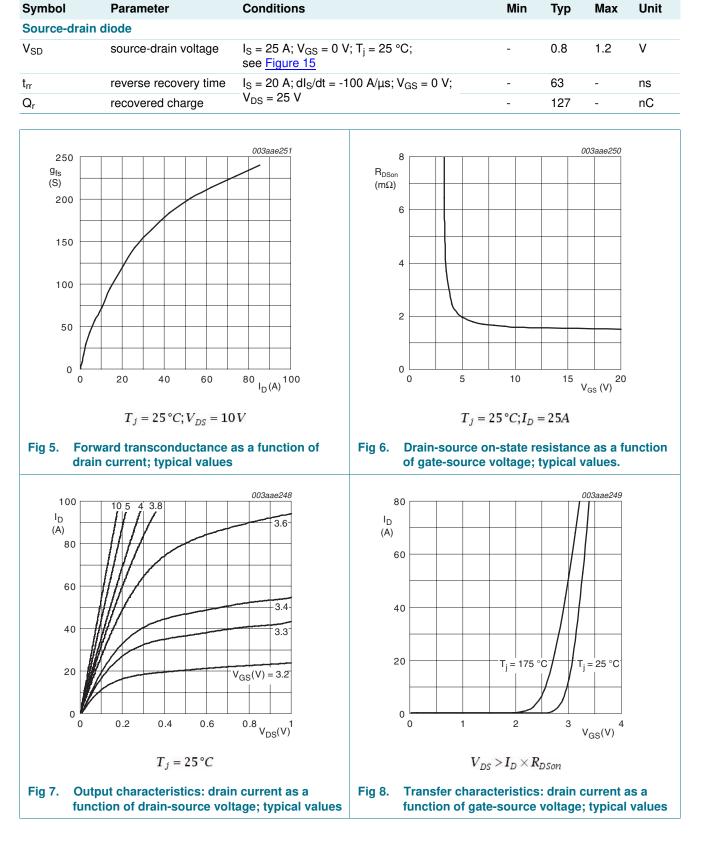
| Symbol                         | Parameter                        | Conditions   | Min | Тур  | Max  | Unit |
|--------------------------------|----------------------------------|--|-----|------|------|------|
| Static chara                   | acteristics                      |  |     |      |      |      |
| V <sub>(BR)DSS</sub>           | drain-source                     | $I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$  | 40  | -    | -    | V    |
|                                | breakdown voltage                | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$   | 36  | -    | -    | V    |
| V <sub>GS(th)</sub>            | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C;<br>see <u>Figure 9</u> ; see <u>Figure 10</u> | 1.8 | 2.3  | 2.8  | V    |
|                                |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C;<br>see <u>Figure 10</u>                      | -   | -    | 3.3  | V    |
|                                |                                  | I <sub>D</sub> = 2.5 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C;<br>see <u>Figure 10</u>                    | 0.8 | -    | -    | V    |
| DSS drain leakage current      |                                  | $V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C  | -   | -    | 500  | μA   |
|                                |                                  | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -   | 0.02 | 1    | μA   |
| I <sub>GSS</sub>               | gate leakage current             | $V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \ ^{\circ}C$  | -   | 2    | 100  | nA   |
|                                |                                  | $V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \ ^{\circ}C$   | -   | 2    | 100  | nA   |
|                                | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>see <u>Figure 11</u>                                   | -   | 1.6  | 1.9  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>see <u>Figure 11</u>                                    | -   | 2    | 2.6  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>see <u>Figure 11</u>                                  | -   | 2.25 | 3.1  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C;<br>see <u>Figure 12</u> ; see <u>Figure 11</u>           | -   | -    | 4    | mΩ   |
| Dynamic ch                     | aracteristics                    |  |     |      |      |      |
| $Q_{G(tot)}$ total gate charge |                                  | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$<br>see <u>Figure 13</u> ; see <u>Figure 14</u>               | -   | 260  | -    | nC   |
|                                |                                  | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$<br>see <u>Figure 13</u> ; see <u>Figure 14</u>                | -   | 147  | -    | nC   |
| Q <sub>GS</sub>                | gate-source charge               | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$  | -   | 38   | -    | nC   |
| Q <sub>GD</sub>                | gate-drain charge                | see <u>Figure 13;</u> see <u>Figure 14</u>   | -   | 72   | -    | nC   |
| C <sub>iss</sub>               | input capacitance                | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$  | -   | 11.3 | 15.1 | nF   |
| C <sub>oss</sub>               | output capacitance               | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$   | -   | 1447 | 1750 | pF   |
| C <sub>rss</sub>               | reverse transfer capacitance     |  | -   | 1014 | 1390 | pF   |
| d(on)                          | turn-on delay time               | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$  | -   | 60   | -    | ns   |
| t <sub>r</sub>                 | rise time                        | $R_{G(ext)} = 10 \ \Omega$   | -   | 140  | -    | ns   |
| d(off)                         | turn-off delay time              |  | -   | 234  | -    | ns   |
| <sup>i</sup> f                 | fall time                        |  | -   | 416  | -    | ns   |
| LD                             | internal drain<br>inductance     | from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$   | -   | 3.5  | -    | nH   |
| L <sub>S</sub>                 | internal source<br>inductance    | from source lead to source bond pad;<br>T <sub>j</sub> = 25 °C   | -   | 7.5  | -    | nH   |

Table 6.

Characteristics ... continued

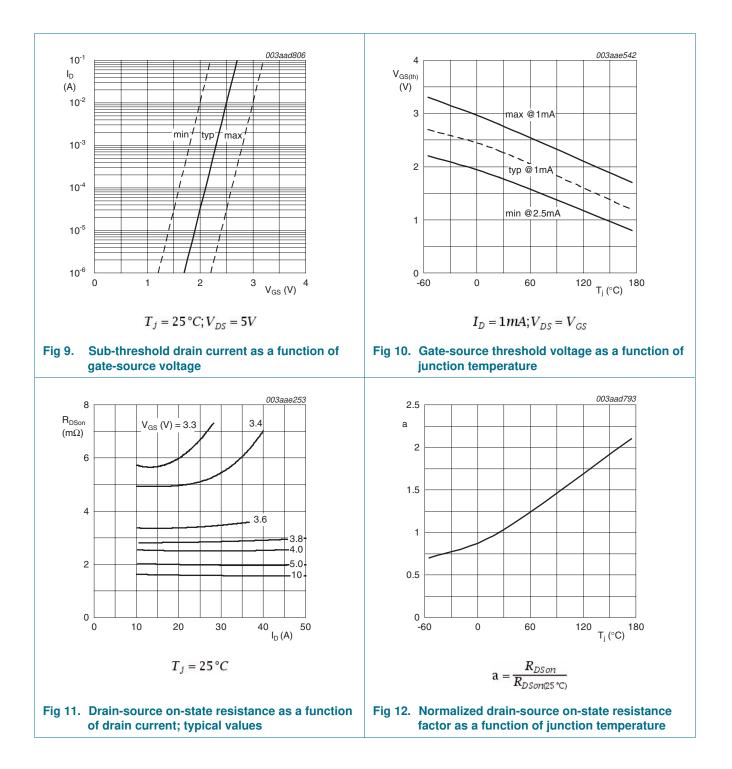
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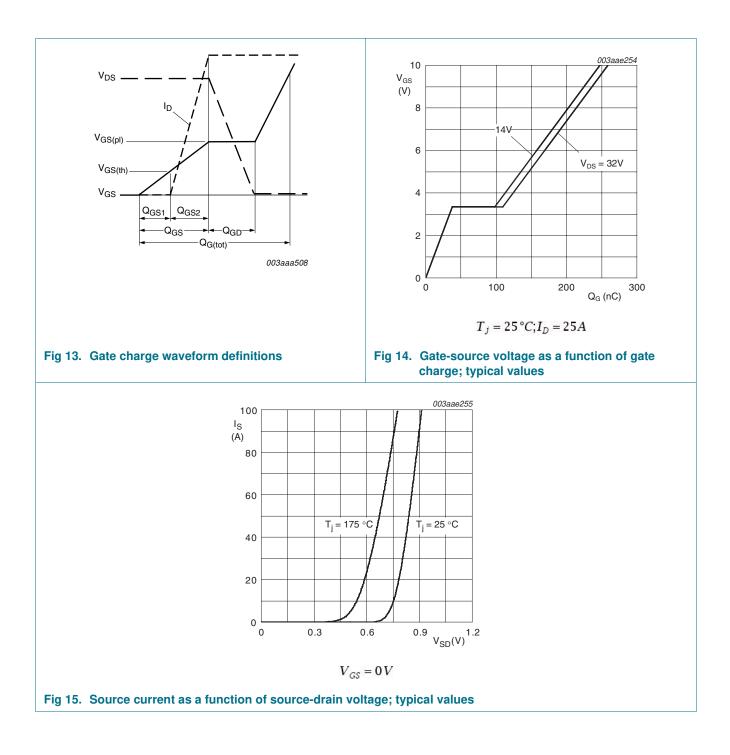


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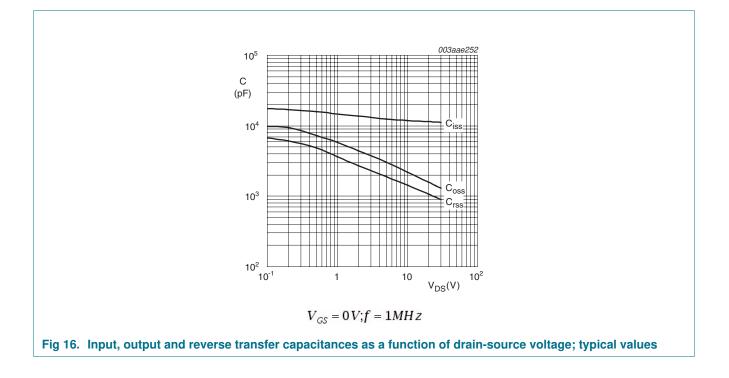
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### 7. Package outline

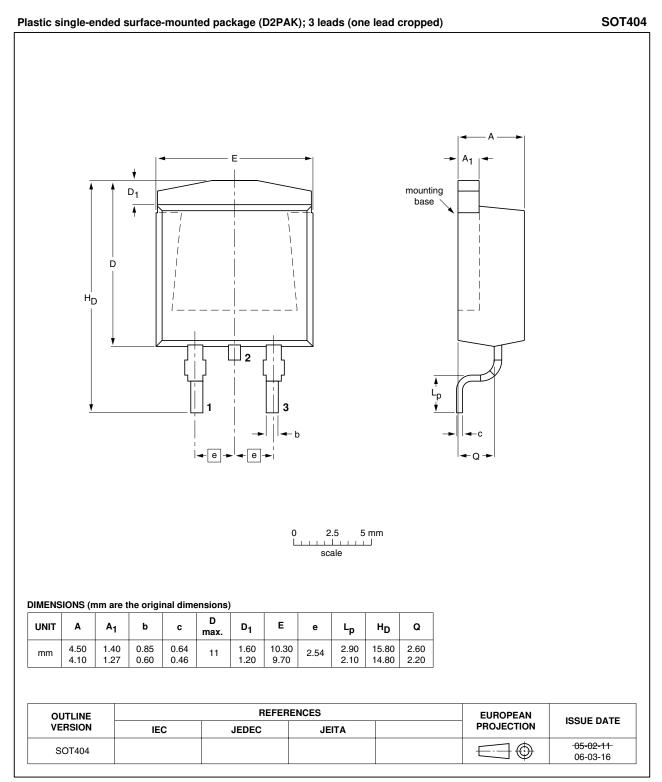


Fig 17. Package outline SOT404 (D2PAK)

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### 8. Revision history

| Table 7. Revision h | Revision history |                    |               |            |  |  |  |
|---------------------|------------------|--------------------|---------------|------------|--|--|--|
| Document ID         | Release date     | Data sheet status  | Change notice | Supersedes |  |  |  |
| BUK661R9-40C v.1    | 20100818         | Product data sheet | -             | -          |  |  |  |

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### 9.1 Data sheet status

| Document status[1][2]          | Product status <sup>[3]</sup> | Definition  |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet   | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

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